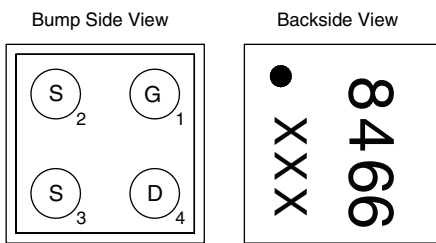


N-Channel 8 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A) ^{a, e}	Q _g (Typ.)
8	0.043 at V _{GS} = 4.5 V	5.4	6.8 nC
	0.046 at V _{GS} = 2.5 V	5.2	
	0.060 at V _{GS} = 1.5 V	4.6	
	0.090 at V _{GS} = 1.2 V	3.0	

MICRO FOOT



Device Marking: 8466
xxx = Date/Lot Traceability Code

Ordering Information:
Si8466EDB-T2-E1 (Lead (Pb)-free and Halogen-free)

FEATURES

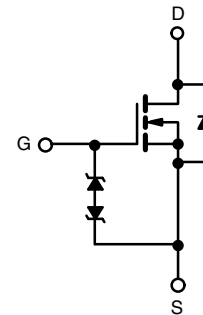
- TrenchFET[®] Power MOSFET
- Typical ESD protection 3000 V HBM
- Ultra-Small 1 mm x 1 mm maximum Outline
- Ultra-Thin 0.548 mm maximum height
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Low On-Resistance Load Switch for Portable Devices
 - Low Power Consumption,
 - Low Voltage Drop
 - Increased Battery Life
 - Space Savings on PCB



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	8	V	
Gate-Source Voltage	V _{GS}	± 5		
Continuous Drain Current (T _J = 150 °C)	I _D	T _A = 25 °C	5.4 ^a	A
		T _A = 70 °C	4.4 ^a	
		T _A = 25 °C	3.6 ^b	
		T _A = 70 °C	2.9 ^b	
Pulsed Drain Current (t = 300 μs)	I _{DM}	20		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	1.5 ^a	
		T _A = 25 °C	0.65 ^b	
Maximum Power Dissipation	P _D	T _A = 25 °C	1.8 ^a	W
		T _A = 70 °C	1.1 ^a	
		T _A = 25 °C	0.78 ^b	
		T _A = 70 °C	0.5 ^b	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		
Package Reflow Conditions ^c	VPR	260	°C	
	IR/Convection	260		

Notes:

- Surface mounted on 1" x 1" FR4 board with full copper, t = 10 s.
- Surface mounted on 1" x 1" FR4 board with minimum copper, t = 10 s.
- Refer to IPC/JEDEC (J-STD-020), no manual or hand soldering.
- In this document, any reference to case represents the body of the MICRO FOOT device and foot is the bump.
- Based on T_A = 25 °C.

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, b}	$t = 10 \text{ s}$	R_{thJA}	55	70	°C/W
Maximum Junction-to-Ambient ^{c, d}	$t = 10 \text{ s}$		125	160	

Notes:

- a. Surface mounted on 1" x 1" FR4 board with full copper.
b. Maximum under steady state conditions is 100 °C/W.
c. Surface mounted on 1" x 1" FR4 board with minimum copper.
d. Maximum under steady state conditions is 190 °C/W.

SPECIFICATIONS ($T_J = 25 \text{ °C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \text{ } \mu\text{A}$	8			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250 \text{ } \mu\text{A}$		3.5		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-3			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \text{ } \mu\text{A}$	0.35		0.7	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			± 3	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 8 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
		$V_{DS} = 8 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 70 \text{ °C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5 \text{ V}, I_D = 2 \text{ A}$		0.035	0.043	Ω
		$V_{GS} = 2.5 \text{ V}, I_D = 1 \text{ A}$		0.037	0.046	
		$V_{GS} = 1.5 \text{ V}, I_D = 1 \text{ A}$		0.045	0.060	
		$V_{GS} = 1.2 \text{ V}, I_D = 0.5 \text{ A}$		0.055	0.090	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 4 \text{ V}, I_D = 2 \text{ A}$		30		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 4 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		710		pF
Output Capacitance	C_{oss}			270		
Reverse Transfer Capacitance	C_{rss}			192		
Total Gate Charge	Q_g	$V_{DS} = 4 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 2 \text{ A}$		8.5	13	nC
Gate-Source Charge	Q_{gs}			0.9		
Gate-Drain Charge	Q_{gd}			1.6		
Gate Resistance	R_g	$V_{GS} = 0.1 \text{ V}, f = 1 \text{ MHz}$		6		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 4 \text{ V}, R_L = 2 \text{ } \Omega$ $I_D \cong 2 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \text{ } \Omega$		10	20	ns
Rise Time	t_r			15	30	
Turn-Off Delay Time	$t_{d(off)}$			40	80	
Fall Time	t_f			10	20	

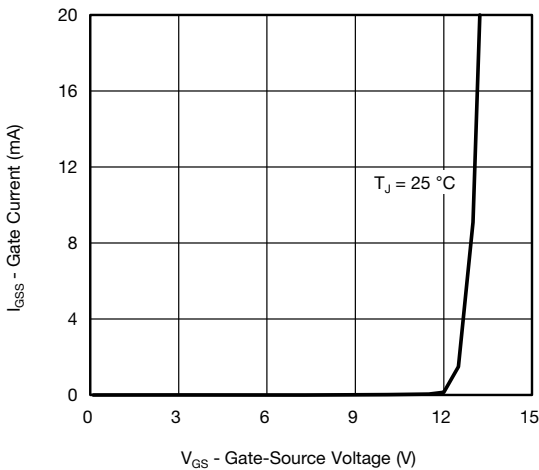
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_A = 25\text{ }^\circ\text{C}$			1.5	A
Pulse Diode Forward Current	I_{SM}				20	
Body Diode Voltage	V_{SD}	$I_S = 1.5\text{ A}, V_{GS} = 0$		0.7	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 2\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		30	60	ns
Body Diode Reverse Recovery Charge	Q_{rr}			7	15	nC
Reverse Recovery Fall Time	t_a			15		ns
Reverse Recovery Rise Time	t_b			15		

Notes:

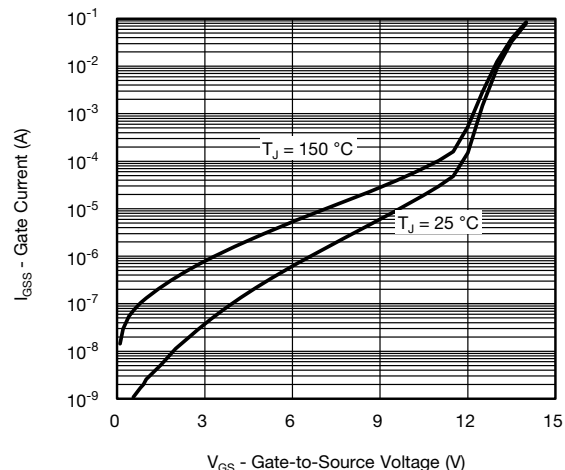
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS ($25\text{ }^\circ\text{C}$, unless otherwise noted)

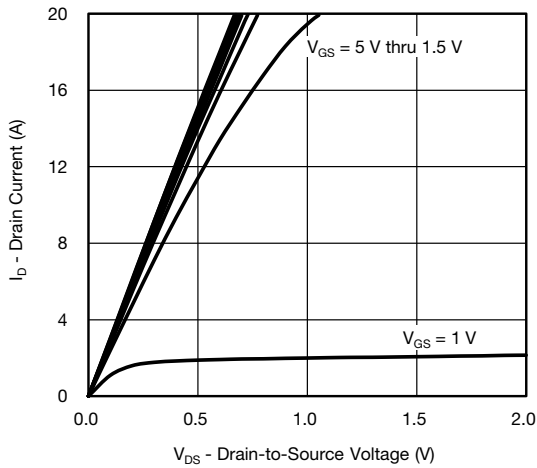


Output Characteristics

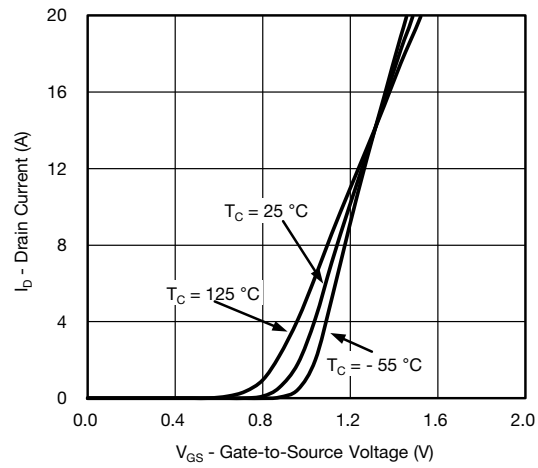


On-Resistance vs. Drain Current and Gate Voltage

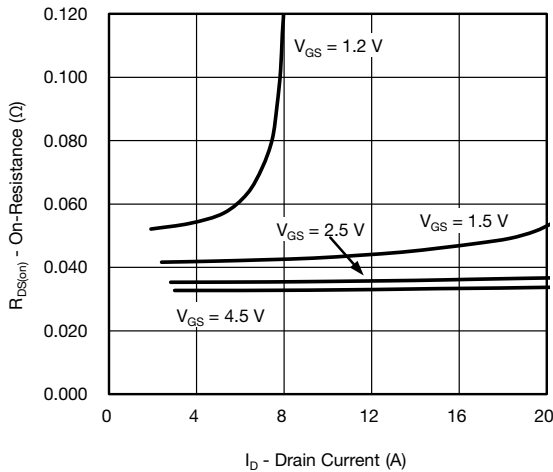
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



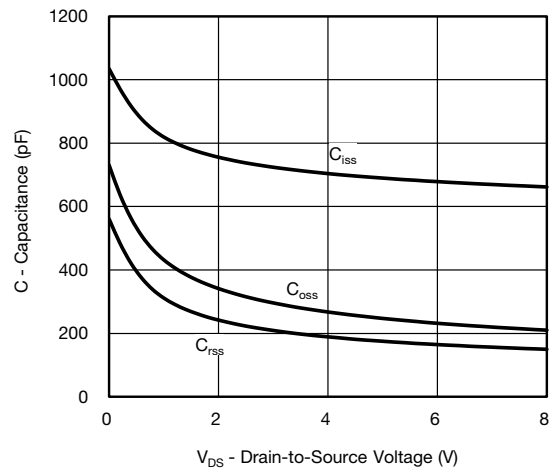
Output Characteristics



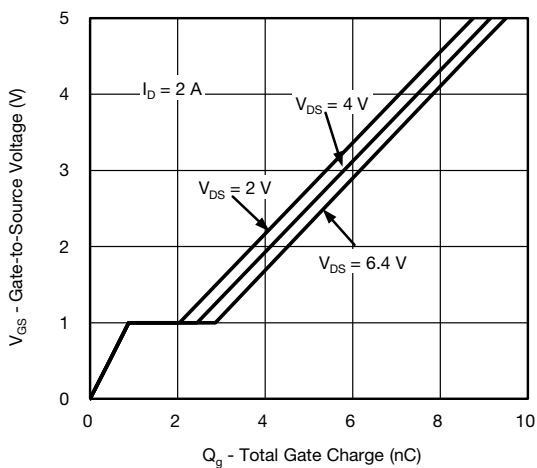
Transfer Characteristics



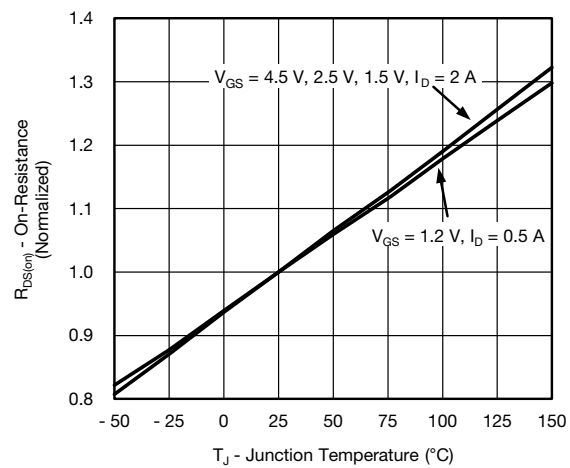
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

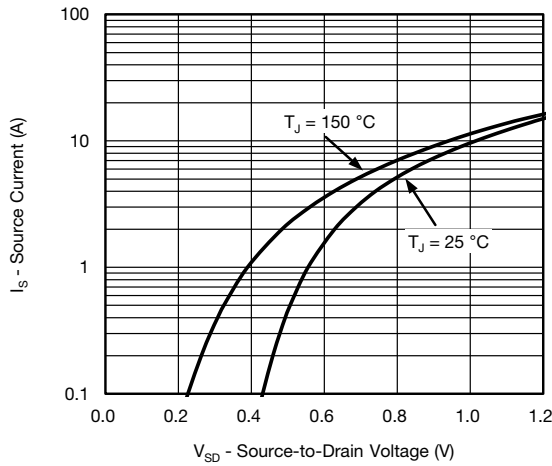


Gate Charge

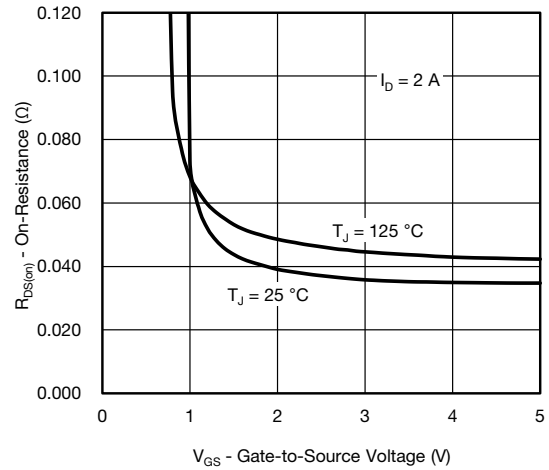


On-Resistance vs. Junction Temperature

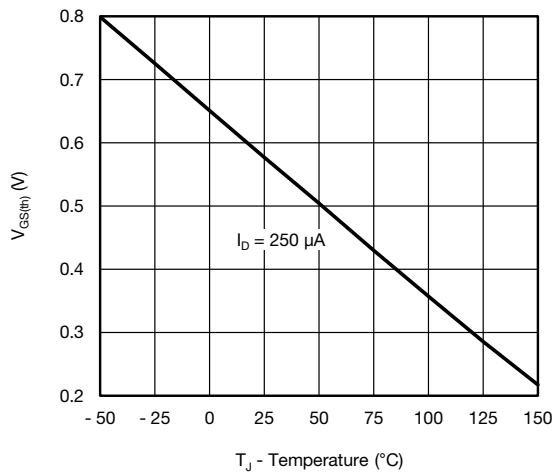
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



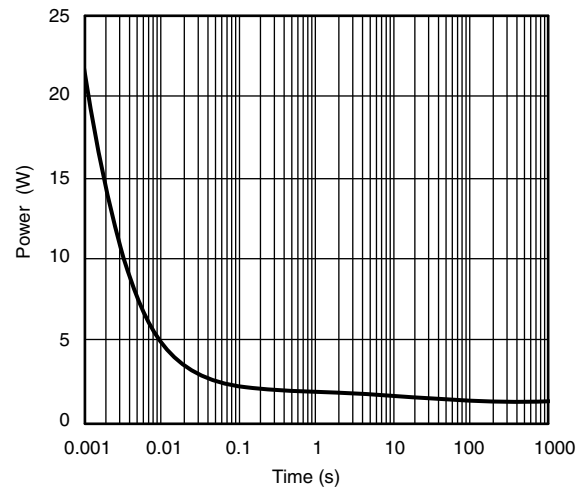
Source-Drain Diode Forward Voltage



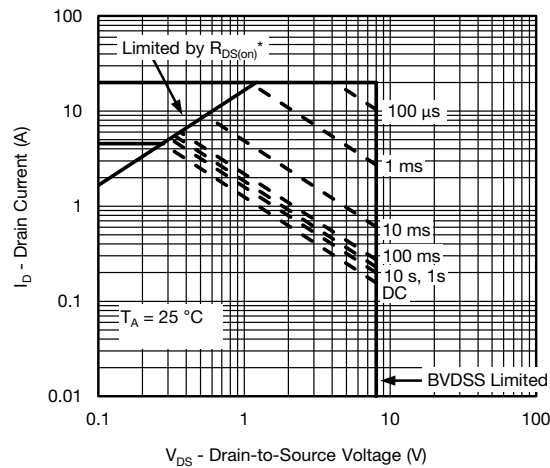
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

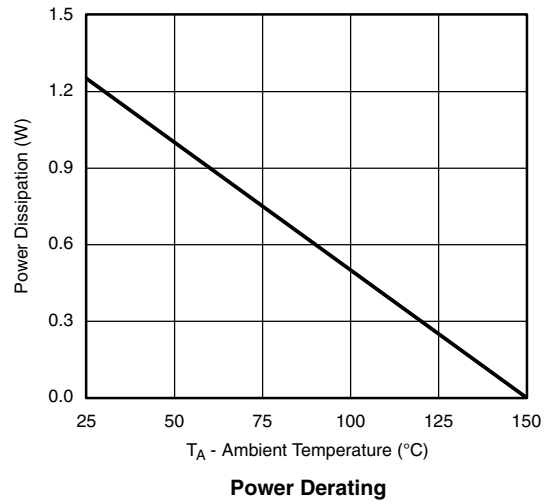
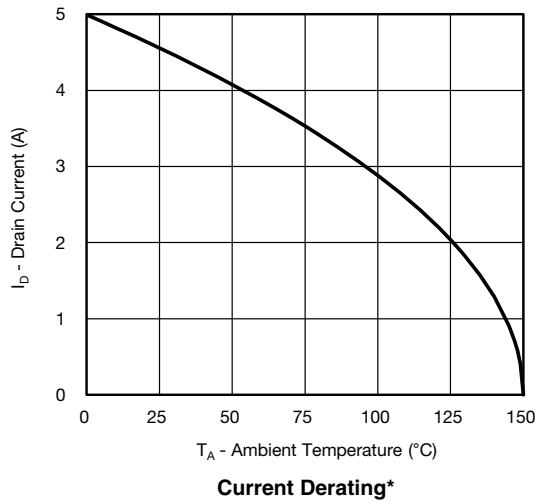


Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

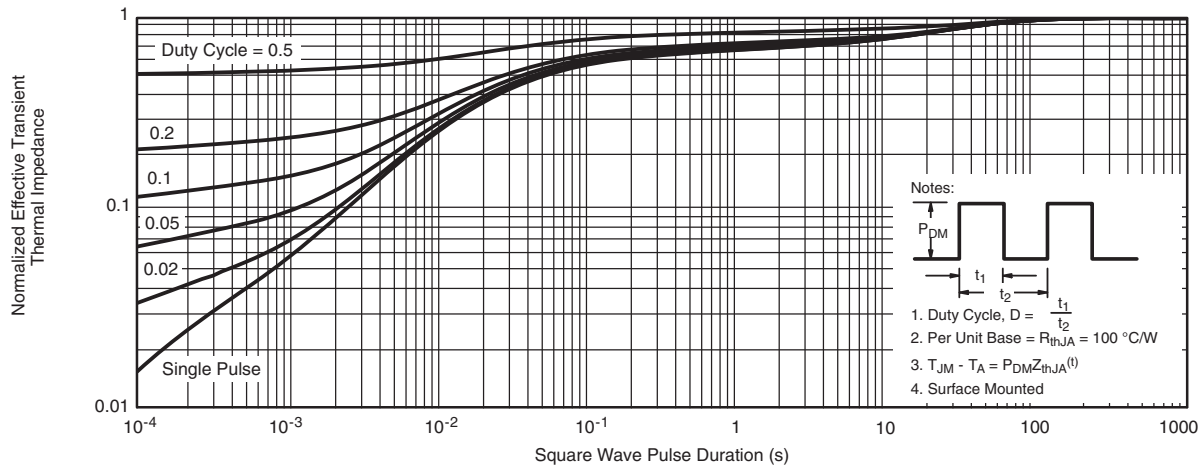
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



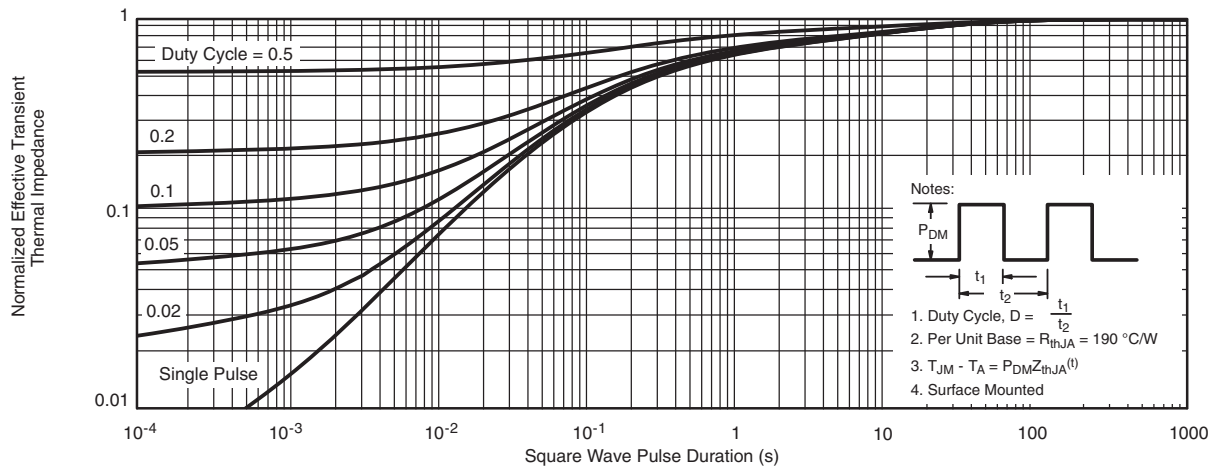
Note:
When Mounted on 1" x 1" FR4 with Full Copper.

* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



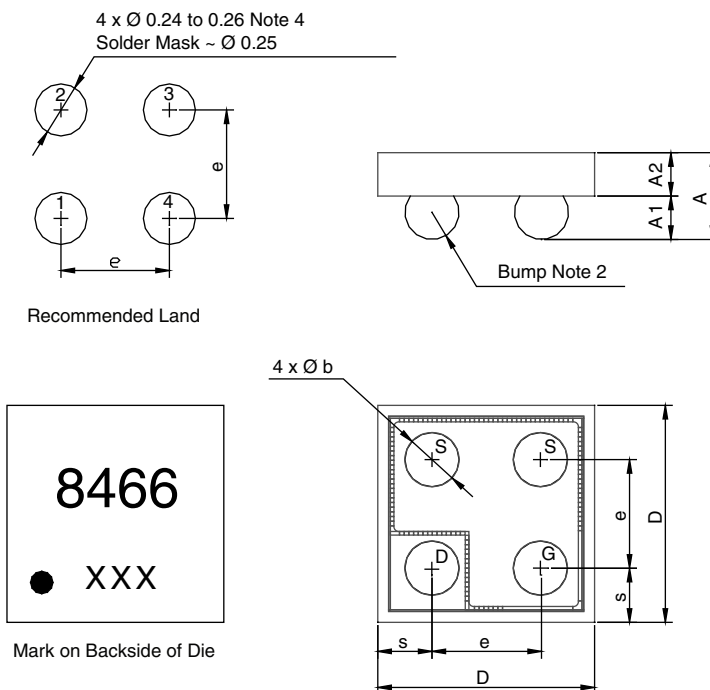
Normalized Thermal Transient Impedance, Junction-to-Ambient (1" x 1" FR4 Board with Full Copper)



Normalized Thermal Transient Impedance, Junction-to-Ambient (1" x 1" FR4 Board with Minimum Copper)

PACKAGE OUTLINE

MICRO FOOT 1 mm x 1 mm: 4-BUMP (2 x 2, 0.5 mm PITCH)



Notes (Unless otherwise specified):

1. All dimensions are in millimeters.
2. Four (4) solder bumps are lead (Pb)-free 95.5Sn/3.8Ag/0.7Cu with diameter \varnothing 0.30 mm to 0.32 mm.
3. Backside surface is coated with a Ti/Ni/Ag layer.
4. Non-solder mask defined copper landing pad.
5. • is location of pin 1.

Dim.	Millimeters ^a			Inches		
	Min.	Nom.	Max.	Min.	Nom.	Max.
A	0.462	0.505	0.548	0.0181	0.0198	0.0215
A ₁	0.220	0.250	0.280	0.0086	0.0098	0.0110
A ₂	0.242	0.255	0.268	0.0095	0.0100	0.0105
b	0.300	0.310	0.320	0.0118	0.0122	0.0126
e	0.500			0.0197		
s	0.230	0.250	0.270	0.0090	0.0098	0.0106
D	0.920	0.960	1.000	0.0362	0.0378	0.0394

Notes:

- a. Use millimeters as the primary measurement.

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